

ABSTRACT OF THE DISCLOSURE

A method of photoresist removal is described. A substrate is located in a processing chamber. A mixture of gases is excited, the mixture comprising a majority component of a reducing process gas and a minority component of between 0.1% and 10% by volume of an oxidizing process gas. Reactive gas species are thereby generated. A photoresist layer with an exposed dielectric layer on the substrate in the chamber is then exposed to the reactive gas mixture to selectively remove the photoresist layer from the dielectric layer.